

a	Acceleration	I_{DSS}	Drain source leakage current
BV_{CES}	Collector emitter breakdown voltage	I_F, I_T	Forward current
BV_{DSS}	Drain source breakdown voltage	I_{FM}	Maximum forward current
C_{ies}, C_{iss}	Input capacitance	I_{FAV}	Average forward current
C_{oes}	Output capacitance	I_{F(AV)M}, I_{T(AV)M}	Maximum average forward current
C_{res}, C_{rss}	Reverse transfer (Miller) capacitance	I_{FLT}	Sink current of fault terminal
d	Duty cycle	I_{FRM}	Maximum repetitive forward current
d_A	Strike distance through air	I_{F(RMS)}, I_{T(RMS)}	RMS forward current
di/dt, -di/dt	Rate of change of current	I_{FSM}, I_{TSM}	Maximum surge forward current
(di/dt)_{cr}	Critical rate of rise of current	I_G, I_{GT}	Trigger gate current
di_F/dt, -di_F/dt	Rate of change of forward current	I_{GD}	Non-trigger gate current
d_S	Creeping distance on surface	I_{GES}	Gate emitter leakage current
dv/dt	Rate of rise of voltage	I_H	Holding current
(dv/dt)_{cr}	Critical rate of rise of voltage	I_{IN(H)}	Signal input current (high level)
E_{AR}	Repetitive avalanche energy	I_{IN(L)}	Signal input current (low level)
E_{AS}	Non-repetitive avalanche energy	I_{ISOL}	RMS current for isolation test
E_{off}	Turn-off energy per pulse	I_L	Latching current
E_{on}	Turn-on energy per pulse	I_R	Reverse current
F_C	Mounting force with clip	I_{RM}	Maximum reverse recovery current
g_{fs}	Forward transconductance	I_{RMS}	RMS current
I_{AR}	Repetitive avalanche current	I_{RRM}	Maximum repetitive reverse current
I_{AVM}	Maximum average forward current	I_S	Continuous source current
I_{BO}	Breakover current	I_{SM}	Maximum pulsed source current
I_{C(on)}	Short circuit current	I²t, J²dt	I ² t value for fusing
I_C	Collector current	I_{TSM}	Maximum surge on-state current
I_{C25}	Continuous DC collector current at T _C = 25°C	K_f	Characteristic factor
I_{C90}	Continuous DC collector current at T _C = 90°C	K_p	Coeff. for energy per pulse E _p (material constant)
I_{CES}	Collector emitter leakage current	K_T	Temperature coefficient of V _{BO}
I_{CM}	Maximum pulsed collector current	L	Series stray inductance
I_D	Drain current	M_d	Mounting torque
I_{DD}	Module supply current, operating mode	P_C	Collector dissipation
I_{DD0}	Module supply current, standby mode	P_D	Power dissipation
I_{D(cont)}	Continuous drain current	P_{GAV}	Average gate power dissipation
I_{D25}	Continuous drain current at T _C = 25°C	P_{G(AV)M}	Maximum average gate power dissipation
I_{DAV}	Average DC output current	P_{GM}	Maximum gate power dissipation
I_{D(AV)M}	Maximum average DC output current	P_{RSM}	Maximum surge reverse power dissipation
I_{DM}	Maximum pulsed drain current	P_T, P_{tot}	Total power dissipation
I_{DRM}	Maximum repetitive off-state current		
I_{D(RMS)}	RMS output current		

Q_g	Total gate charge	V_{BO}	Breakover voltage
Q_{gc}	Gate collector (Miller) charge	V_{CE}	Collector emitter voltage
Q_{gd}	Gate drain (Miller) charge	$V_{CE(sat)}$	Collector emitter saturation voltage
Q_{ge}	Gate emitter charge	$V_{CE(sat)FLT}$	Collector emitter saturation voltage to indicate fault
Q_{gs}	Gate source charge	V_{CES}	Collector emitter voltage
Q_r	Recovered charge	V_{CGR}	Collector gate voltage
Q_{RM}	Recovered charge (intrinsic diode)	V_{DD}	Module supply voltage
Q_s	Recovered charge to peak	$V_{DD FLT}$	Module supply voltage without fault
RBSOA	Reverse Bias Safe Operating Area	V_{DGR}	Drain gate voltage
$R_{DS(on)}$	Static drain source on resistance	V_{DRM}	Maximum repetitive forward blocking voltage
RFI	Radio frequency interference (= EMI)	V_{DS}	Drain source voltage
R_G	Gate resistance	V_{DSM}	Maximum non-repetitive forward blocking voltage
R_{GE}	Gate emitter resistance	V_{DSS}	Drain source breakdown voltage
r_T	Slope resistance (for power loss calculation only)	Version	Various construction designs of products
$R_{thCK}; R_{thCH}$	Thermal resistance case to heatsink	V_F	Forward voltage
R_{thJA}	Thermal resistance junction to ambient	V_{FLT}	Voltage at fault terminal
R_{thJC}	Thermal resistance junction to case	V_{FR}	Forward recovery voltage
$R_{thJK}; R_{thJH}$	Thermal resistance junction to heatsink	V_{GD}	Gate non-trigger voltage
R_{thJS}	Thermal resistance junction to heatsink	V_{GE}	Gate emitter voltage
R_{thJW}	Thermal resistance junction to water	$V_{GE(th)}$	Gate emitter threshold voltage
R_{thKA}	Thermal resistance heatsink to ambient	V_{GEM}	Maximum transient collector gate voltage
SCSOA	Short Circuit Safe Operating Area	V_{GES}	Maximum DC gate voltage
T_{amb}, T_A	Ambient (cooling medium) temperature	V_{GS}	Gate source voltage
T_C, T_{case}	Case temperature	$V_{GS(th)}$	Gate threshold voltage
$t_{d(off)}$	Turn-off delay time	V_{GSM}	Maximum transient gate source voltage
$t_{d(on)}$	Turn-on delay time	V_{GT}	Gate trigger voltage
t_{fi}	Overcurrent or short circuit trip delay time	V_H	Holding voltage
t_{fr}	Forward recovery time	V_{IN}	Input control voltage
t_{FLT}	Overcurrent or short circuit trip delay time	$V_{IN(H)}$	Input voltage threshold for IGBT turn-on
t_{gd}	Gate controlled delay time	$V_{IN(L)}$	Input voltage threshold for IGBT turn-off
T_J, T_{VJ}	Virtual junction temperature	V_{ISOL}	Isolation voltage
T_{JM}, T_{VJM}	Maximum virtual junction temperature	V_R	Reverse voltage
T_K, T_H, T_S	Heatsink temperature	V_{RES}	Input voltage threshold for Reset = active
T_L	Lead temperature	V_{RGM}	Maximum reverse gate voltage
$T_{S(max)}$	Maximum allowable heatsink temperature	V_{RRM}	Maximum repetitive reverse voltage
T_{stg}	Storage temperature	V_{RSM}	Maximum non-repetitive reverse voltage
t_p	Pulse time	V_{SD}	Forward voltage drop
t_q	Turn-off time	V_T	Forward voltage
t_r	Current rise time	V_{TO}	Threshold voltage (for power loss calculation only)
t_{rr}	Reverse recovery time	Z_{thJC}	Transient thermal impedance junction to case
t_{rv}	Rise time of collector emitter voltage	Z_{thJK}, Z_{thJH}	Transient thermal impedance junction to heatsink
t_{SC}	Short circuit duration		